
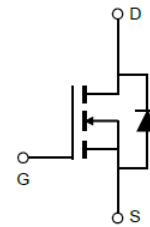
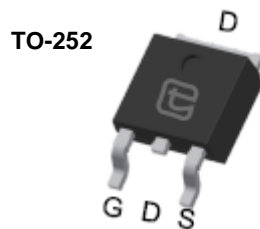


**85V N-Channel Trench MOSFET**

<p>General Description</p> <ul style="list-style-type: none"> ● Trench Power technology ● Low $R_{DS(ON)}$ ● Low Gate Charge ● Optimized for fast-switching applications <p>Applications</p> <ul style="list-style-type: none"> ● Synchronous Rectification in DC/DC and AC/DC Converters ● Isolated DC/DC Converters in Telecom and Industrial 	<p>Product Summary</p> <table style="width: 100%; border: none;"> <tr> <td style="width: 60%;">V_{DS}</td> <td style="text-align: right;">85V</td> </tr> <tr> <td>I_D (at $V_{GS}=10V$)</td> <td style="text-align: right;">115A</td> </tr> <tr> <td>$R_{DS(ON)}$ (at $V_{GS}=10V$)</td> <td style="text-align: right;">$< 8.5m\Omega$</td> </tr> </table> <p>100% UIS Tested</p> <div style="text-align: right;"></div>	V_{DS}	85V	I_D (at $V_{GS}=10V$)	115A	$R_{DS(ON)}$ (at $V_{GS}=10V$)	$< 8.5m\Omega$
V_{DS}	85V						
I_D (at $V_{GS}=10V$)	115A						
$R_{DS(ON)}$ (at $V_{GS}=10V$)	$< 8.5m\Omega$						



Part Number	Package Type	Form	Marking
TTD115N08A	TO-252	Tape & Reel	115N08A

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	85	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ^B	I_D	$T_C = 25^\circ\text{C}$	46
		$T_C = 100^\circ\text{C}$	46
Pulsed Drain Current ^A	I_{DM}	460	A
Avalanche Current ^A	I_{AS}	45	A
Single Pulse Avalanche Energy $L = 0.3\text{mH}$ ^A	E_{AS}	303	mJ
Power Dissipation ^C	P_D	$T_C = 25^\circ\text{C}$	245
		$T_C = 100^\circ\text{C}$	123
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 175	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Maximum	Units
Maximum Junction-to-Case	$R_{\theta JC}$	0.61	$^\circ\text{C/W}$
Maximum Junction-to-Ambient	$R_{\theta JA}$	100	



Electrical Characteristics($T_J = 25^\circ\text{C}$ unless otherwise noted)							
Symbol	Parameter	Conditions	Value			Units	
			Min	Typ	Max		
STATIC PARAMETERS							
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	85	--	--	V	
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 85\text{V}, V_{GS} = 0\text{V}$	$T_J = 25^\circ\text{C}$	--	--	1	μA
			$T_J = 125^\circ\text{C}$	--	--	100	
I_{GSS}	Gate-Body Leakage Current	$V_{DS} = 0\text{V}, V_{GS} = \pm 20\text{V}$	--	--	± 100	nA	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	2	3	4	V	
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{V}, I_D = 30\text{A}$	--	7.3	8.5	m Ω	
g_{FS}	Forward Transconductance	$V_{DS} = 5\text{V}, I_D = 20\text{A}$	--	38	--	S	
V_{SD}	Diode Forward Voltage	$I_S = 30\text{A}, V_{GS} = 0\text{V}$	--	--	1	V	
I_S	Maximum Body-Diode Continuous Current ^B		--	--	46	A	
DYNAMIC PARAMETERS							
C_{iss}	Input Capacitance	$V_{GS} = 0\text{V}, V_{DS} = 40\text{V}, f = 1\text{MHz}$	--	6710	--	pF	
C_{oss}	Output Capacitance		--	328	--		
C_{rss}	Reverse Transfer Capacitance		--	320	--		
R_g	Gate Resistance	$f = 1\text{MHz}$	--	1.46	--	Ω	
SWITCHING PARAMETERS							
Q_g	Total Gate Charge	$V_{GS} = 10\text{V}, V_{DS} = 40\text{V}, I_D = 20\text{A}$	--	123	--	nC	
Q_{gs}	Gate Source Charge		--	32	--		
Q_{gd}	Gate Drain Charge		--	36	--		
$t_{D(on)}$	Turn-On Delay Time	$V_{GS} = 10\text{V}, V_{DS} = 40\text{V}, I_D = 20\text{A}, R_G = 2.5\Omega$	--	24	--	ns	
t_r	Turn-On Rise Time		--	19	--		
$T_{D(off)}$	Turn-Off Delay Time		--	70	--		
t_f	Turn-Off Fall Time		--	30	--		
t_{rr}	Body Diode Reverse Recovery Time	$I_F = 20\text{A}, di/dt = 100\text{A}/\mu\text{s}$	--	37	--	ns	
Q_{rr}	Body Diode Reverse Recovery Charge		--	58	--	nC	

A. Single pulse width limited by maximum junction temperature.

B. The maximum current rating is package limited.

C. The power dissipation P_D is based on $T_{J(MAX)} = 175^\circ\text{C}$, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

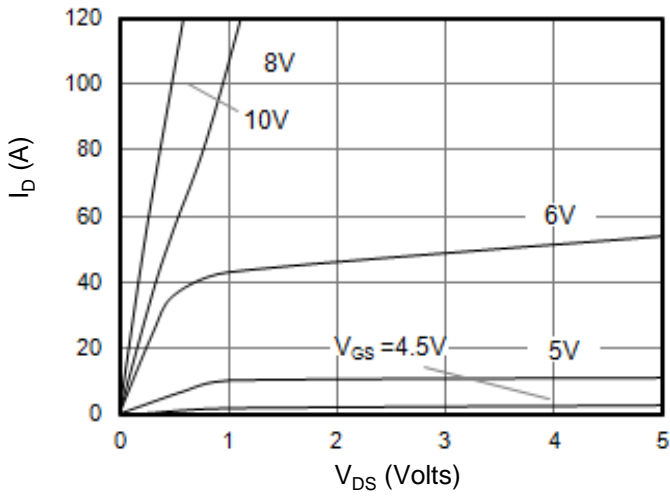


Figure 1: On-Region Characteristics

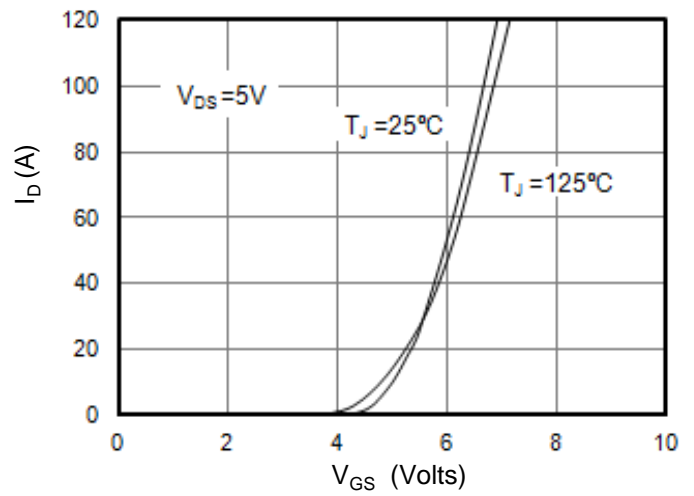


Figure 2: Transfer Characteristics

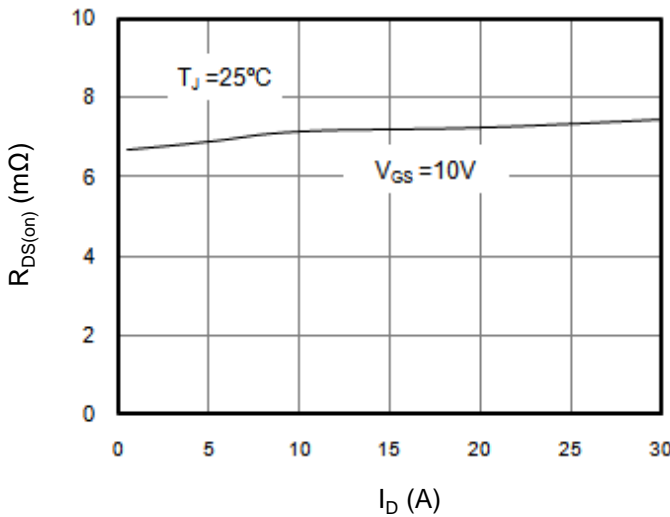


Figure 3: On-Resistance vs. Drain Current

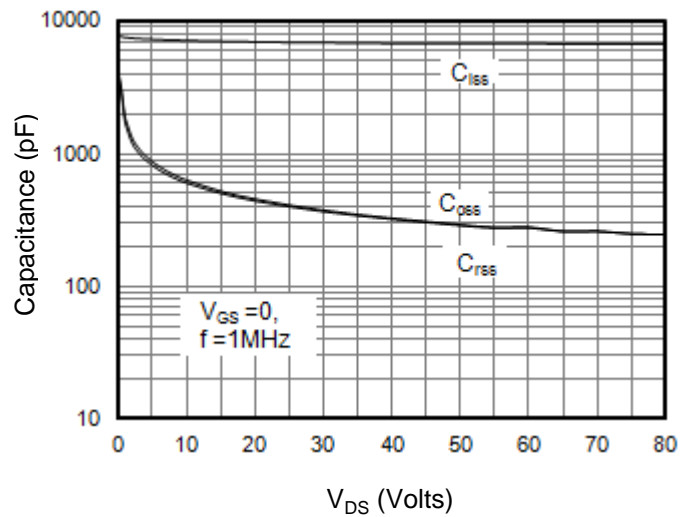


Figure 4: Capacitance Characteristics

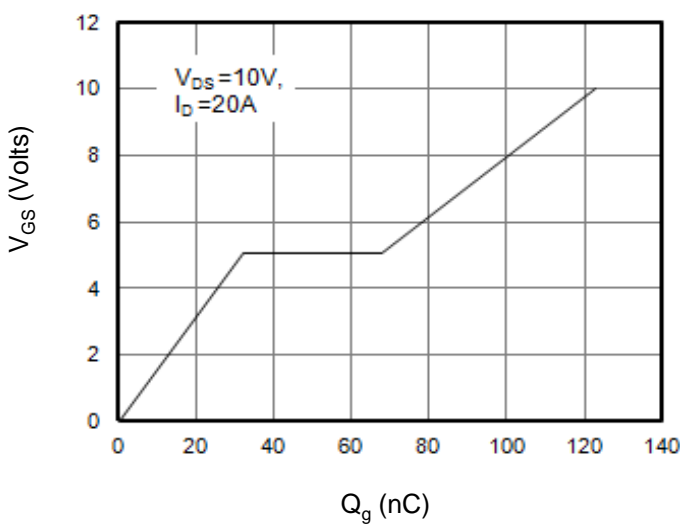


Figure 5: Gate Charge Characteristics

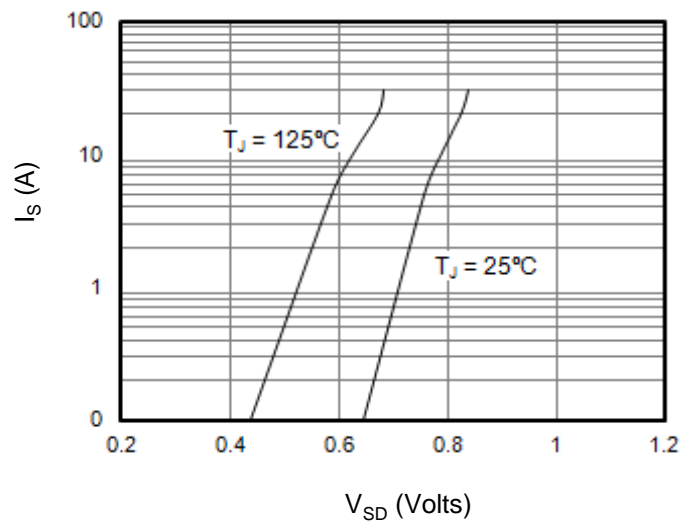


Figure 6: Body Diode Forward Voltage



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

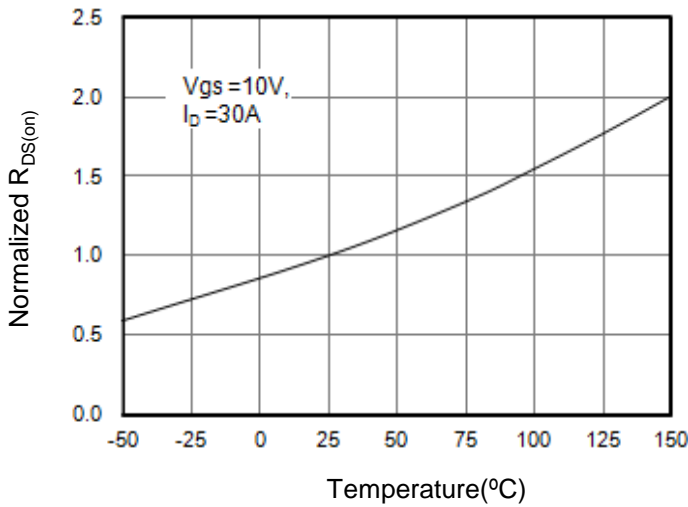


Figure 7: On-Resistance vs. Junction Temperature

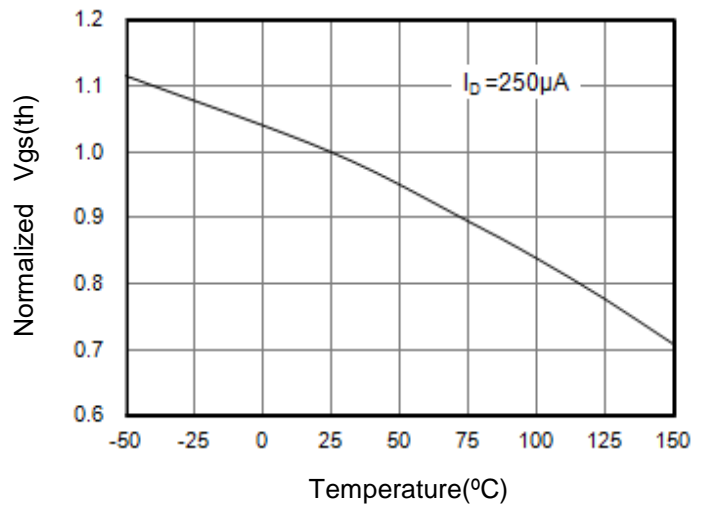


Figure 8: $V_{GS(th)}$ vs. Junction Temperature

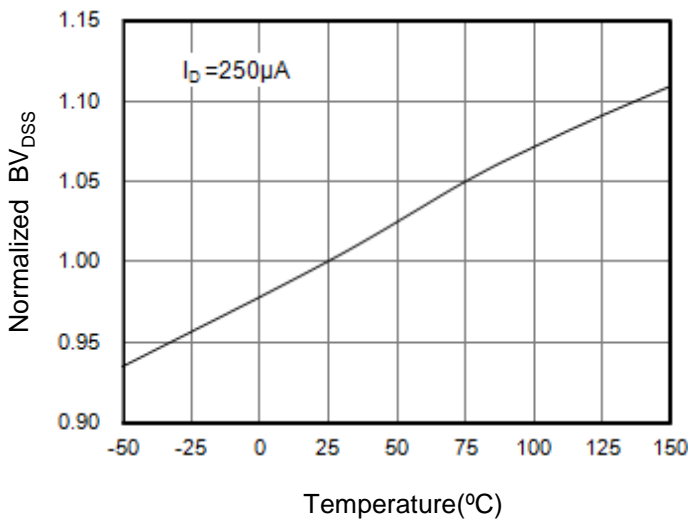


Figure 9: BV_{DS} vs. Junction Temperature

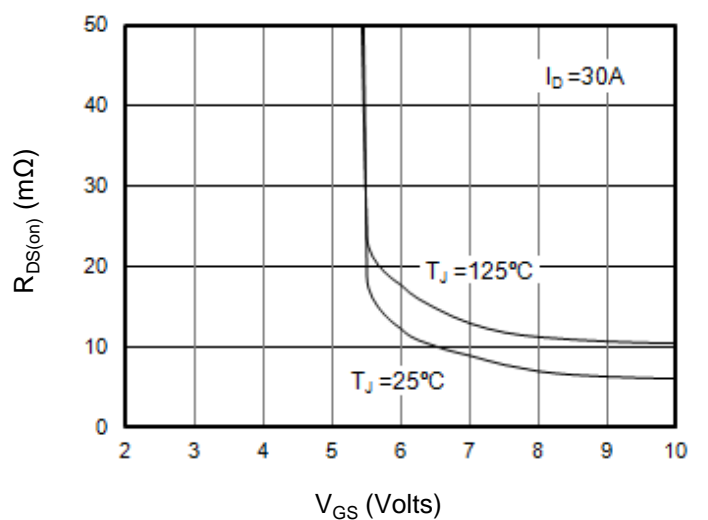


Figure 10: On-Resistance vs. Gate-Source Voltage

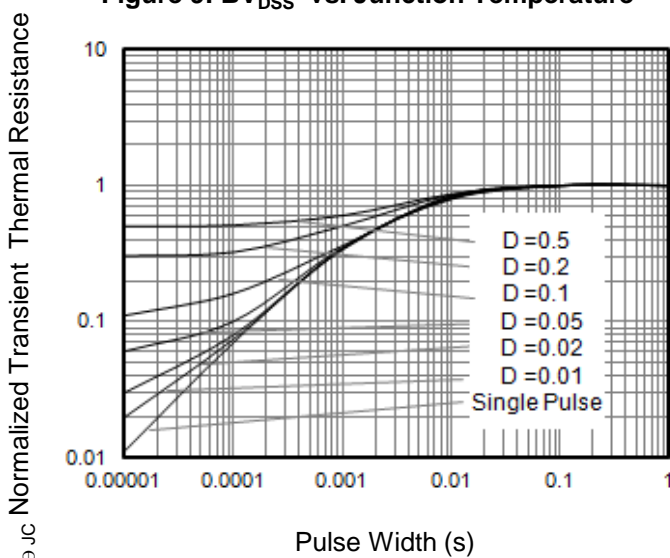


Figure 11: Normalized Transient Thermal Resistance

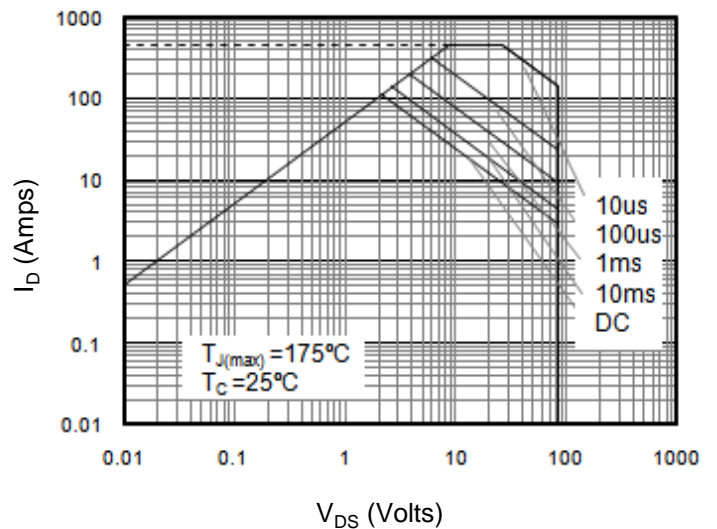


Figure 12: Safe Operating Area



Figure A: Gate Charge Test Circuit and Waveforms

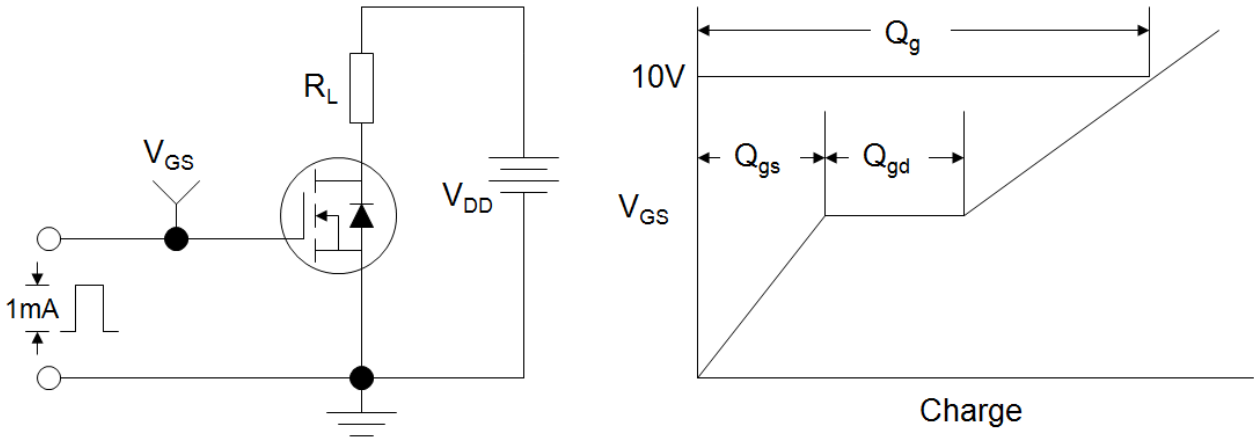


Figure B: Resistive Switching Test Circuit and Waveforms

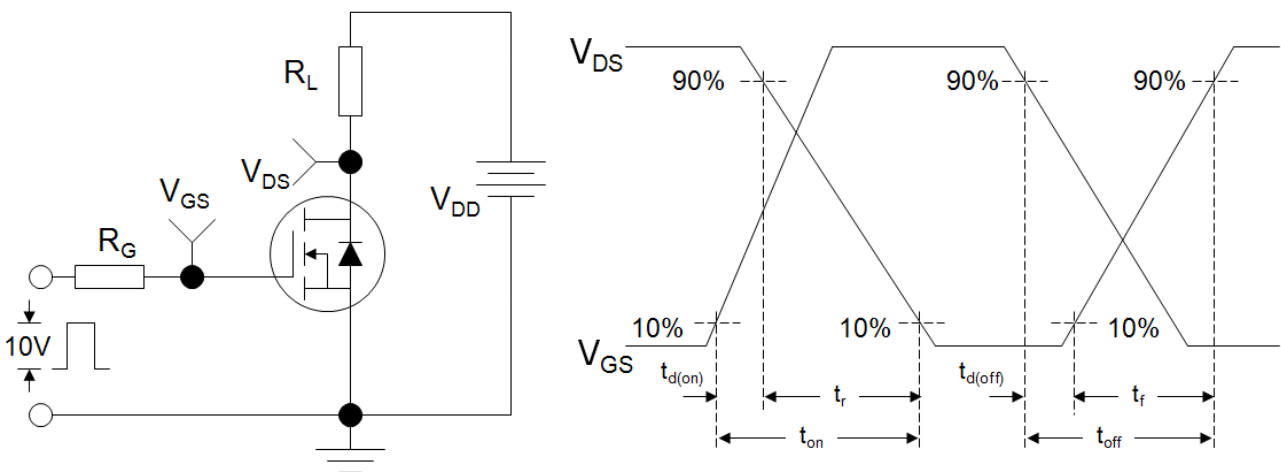
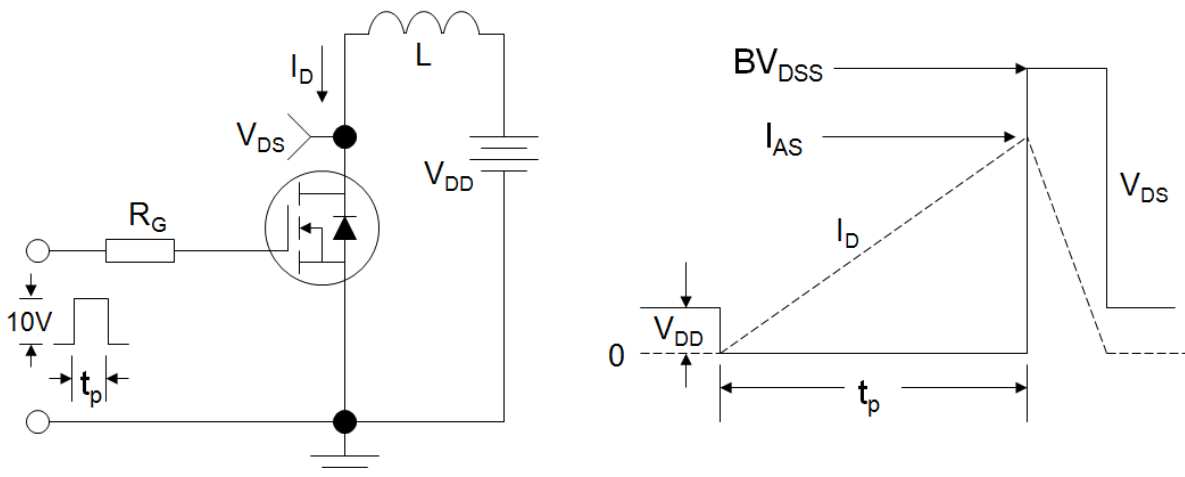
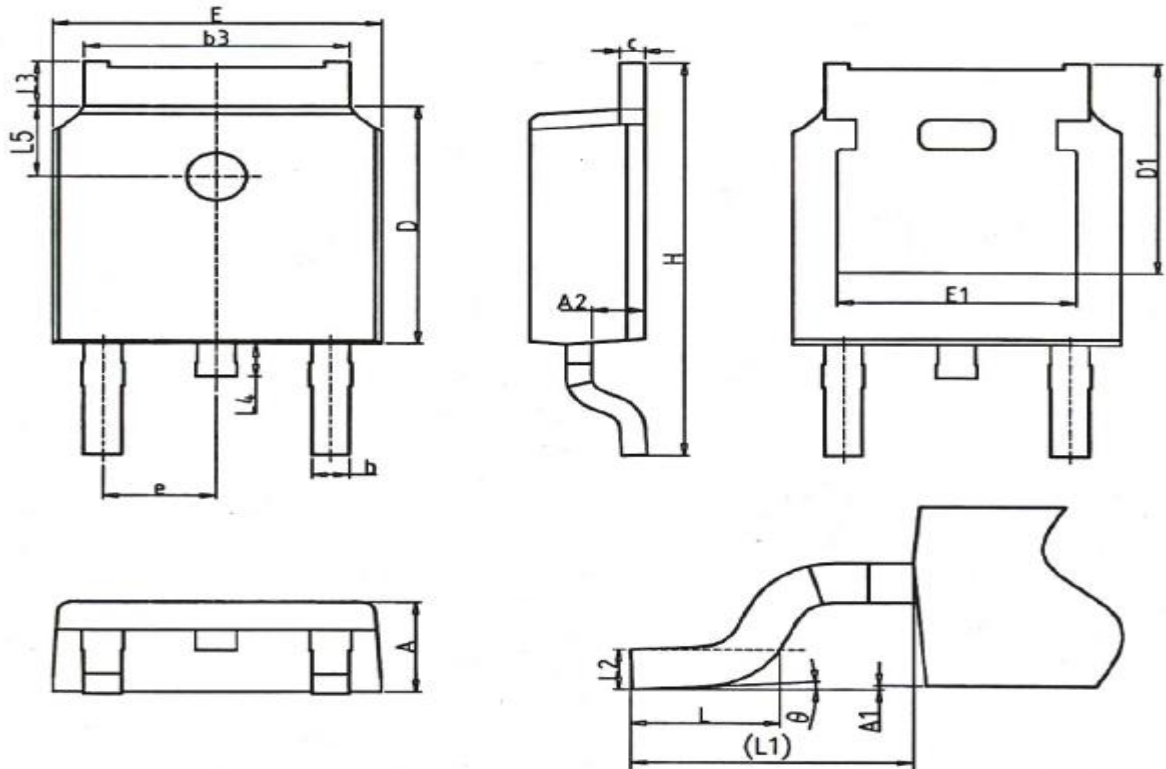


Figure C: Unclamped Inductive Switching (UIS) Test Circuit and Waveforms





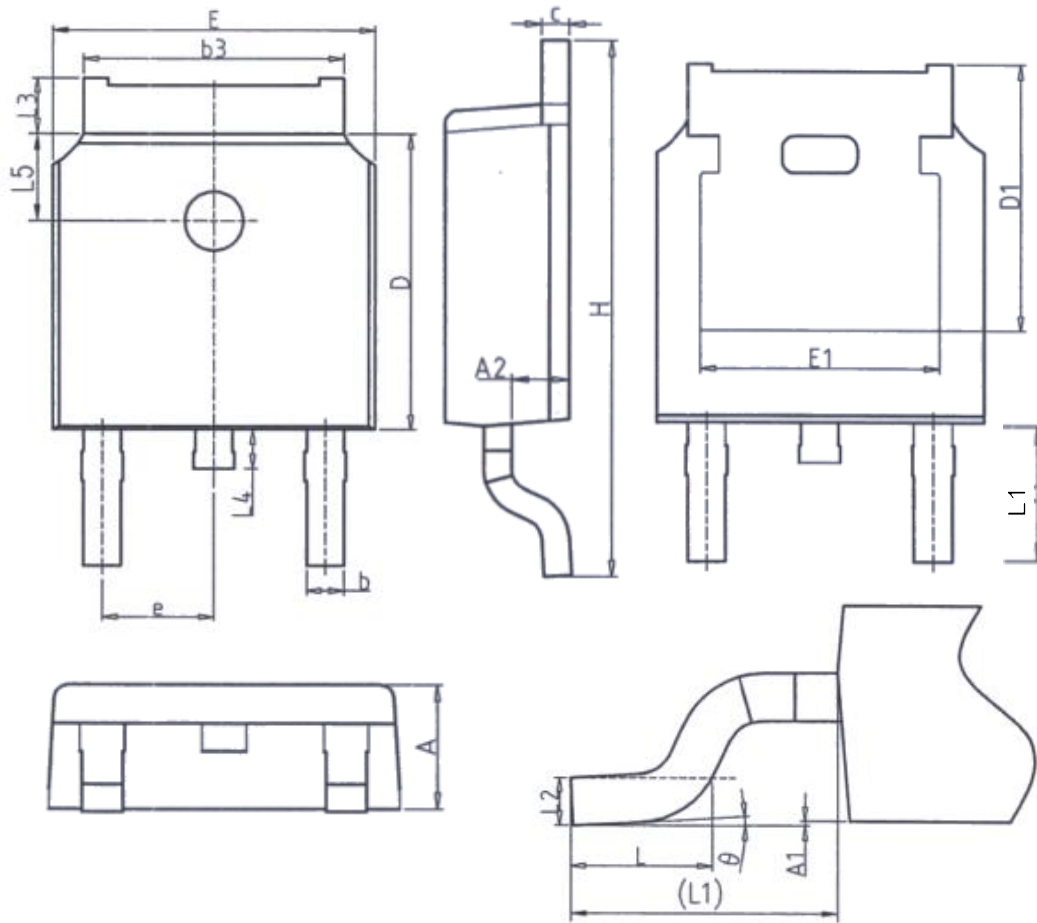
TO-252(海天)



SYMBOL	mm		
	MIN	NOM	MAX
A	2.20	2.30	2.38
A1	0.00	-	0.20
A2	0.97	1.07	1.17
b	0.68	0.78	0.90
b3	5.20	5.33	5.46
c	0.43	0.53	0.61
D	5.98	6.10	6.22
D1	5.30REF		
E	6.40	6.60	6.73
E1	4.63	-	-
e	2.286BSC		
H	9.40	10.10	10.50
L	1.38	1.50	1.75
L1	2.90REF		
L2	0.51BSC		
L3	0.88	-	1.28
L4	0.50	-	1.00
L5	1.65	1.80	1.95
θ	0°	-	8°



TO-252(华羿)



Unit: mm			
Symbol	Min	Nom	Max
A	2.20	2.30	2.38
A1	0.00	-	0.10
A2	0.90	1.01	1.10
b	0.72	-	0.85
b3	5.13	5.33	5.46
c	0.47	-	0.60
D	6.00	6.10	6.20
D1	5.25 REF		
E	6.50	6.60	6.70
E1	4.70	-	-

Unit: mm			
Symbol	Min	Nom	Max
e	2.286BSC		
H	9.80	10.10	10.40
L	1.40	1.50	1.70
L1	2.90REF		
L2	0.508BSC		
L3	0.90	-	1.25
L4	0.60	0.80	1.00
L5	1.8 REF		
θ	0°	-	8°



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